

# FQD19N10TF

## **FQD19N10TF Information**

www.helsener.com	FQD19N10TF Fairchild/ON Semiconductor Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CH 100V 15.6A DPAK TO-252-3, DPak (2 Leads + Tab), SC-63 For the pricing/inventory/lead time, please contact us	
For Reference Only	Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

### **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



### **FQD19N10TF Specifications**

Manufacturer Part NumberFQD19N10TFManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C15.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds780pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)2.5W (Ta), 50W (Tc)Rds On (Max) @ Id, Vgs100 mOhm @ 7.8A, 10V		
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Operating Temperature $-55^{\circ}C \sim 150^{\circ}C (TJ)$		
Mounting Type Surface Mount		
Supplier Device Package D-Pak		
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
	Report errors?	

#### **FQD19N10TF** Guarantees



Quality Guarantees

We provide 90 days warranty. \* If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

#### **FQD19N10TF** Payment Methods



### **FQD19N10TF Shipping Methods**



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